

1-Line Uni-directional TVS Diode

Description

The PESDU1271P6 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive data and power line. PESDU1271P6 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 1.6x1.0x0.5mm lead-free DFN package. The small size and high ESD surge protection make PESDU1271P6 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

Ultra small package: 1.6x1.0x0.5mm

Protects one data or power line

Working Voltage: 12V

Low clamping voltage

· 2-pin leadless package

· Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

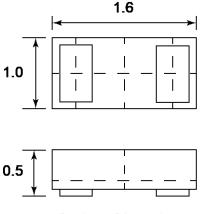
Air discharge: ±30kV

Contact discharge: ±30kV

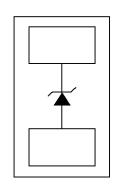
- IEC 61000-4-5 (Lightning) 75A (8/20µs)

RoHS Compliant

Dimensions and Pin Configuration







Circuit and Pin Schematic

Mechanical Characteristics

Package: DFN1610-2

Case Material: "Green" Molding Compound.

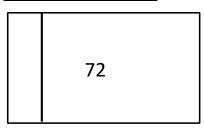
• Moisture Sensitivity: Level 1 per J-STD-020

Marking Information: See Below

Applications

- Mobile Phones and Accessories
- Battery Protection
- USB Power line
- Power Line Protection
- Hand Held Portable Applications

Marking Information



72 = Device Marking Code Bar denotes cathode

Ordering Information

Part Number	Shipping	Reel Size	
PESDU1271P6	3000/Tape & Reel	7 inch	



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

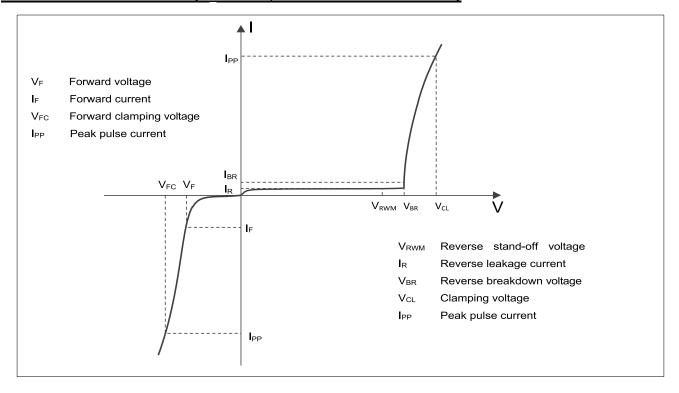
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	P _{PK}	1875	W	
Peak Pulse Current (8/20µs)	Ірр	75	А	
ESD per IEC 61000-4-2 (Air)	.,	±30	kV	
ESD per IEC 61000-4-2 (Contact)	Vesd	±30		
Lead temperature	TL	260	°C	
Operating Temperature Range	Тор	-40 ~ + 85	°C	
Storage Temperature Range	T _{STG}	−55 ~ +150	°C	

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			12	V	
Breakdown Voltage	V_{BR}	12.6			V	I _T = 1mA
Reverse Leakage Current	I _R			1	μΑ	V _{RWM} = 12V
Clamping Voltage	Vc			18	V	I _{PP} = 10A (8/20µs pulse)
Clamping Voltage	Vc			25	V	I _{PP} = 75A (8/20µs pulse)
Junction Capacitance	СJ			500	pF	V _R = 0V, f = 1MHz



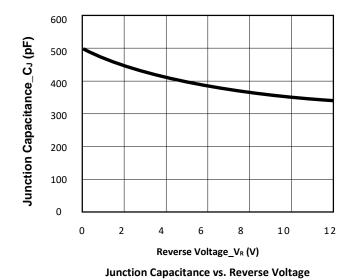
Electrical characteristics (T_A = 25°C, unless otherwise noted)

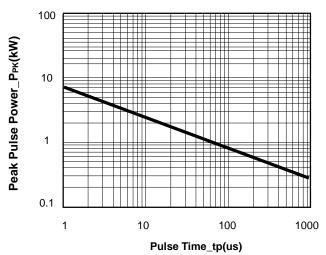


Definitions of electrical characteristics

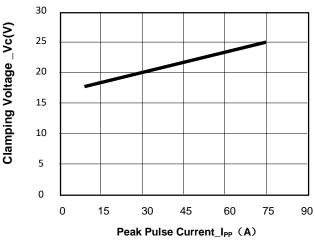


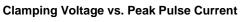
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

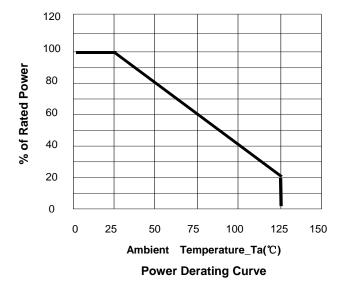


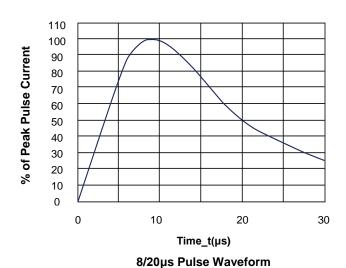


Peak Pulse Power vs. Pulse Time



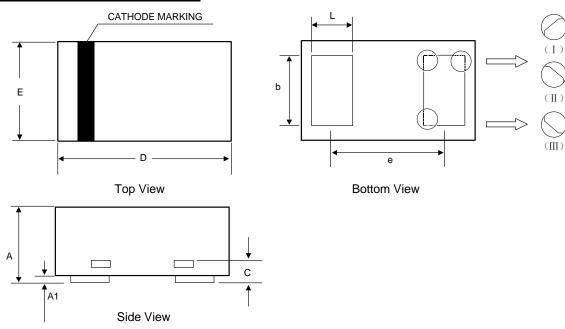






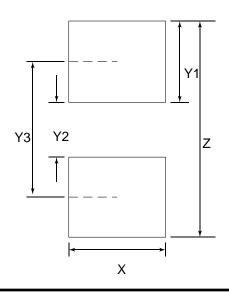


DFN1610-2 Package Outline Drawing



	DIMENSIONS					
SYM	IV	MILLIMETERS		INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
A1		0.02	0.05		0.001	0.002
b	0.75	0.80	0.85	0.030	0.032	0.034
С	0.10	0.15	0.20	0.004	0.006	0.008
D	1.55	1.60	1.65	0.062	0.064	0.066
е	1.10 BSC				0.044 BSC	
Е	0.95	1.00	1.05	0.038	0.040	0.042
L	0.35	0.40	0.45	0.014	0.016	0.018

Suggested Land Pattern

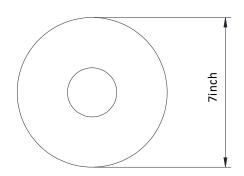


SYM -	DIMENSIONS			
	MILLIMETERS	INCHES		
Х	1.00	0.040		
Y1	0.62	0.025		
Y2	0.60	0.024		
Y3	1.22	0.049		
Z	1.85	0.074		

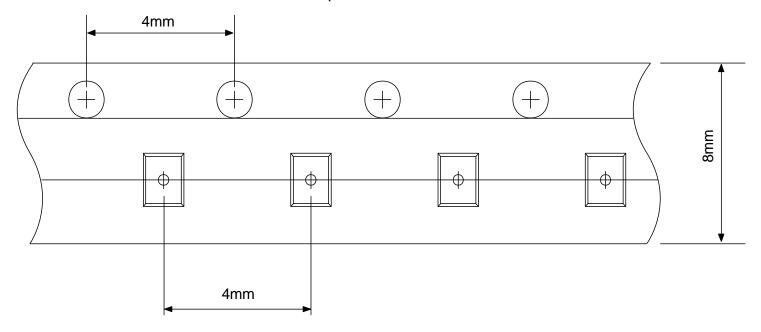


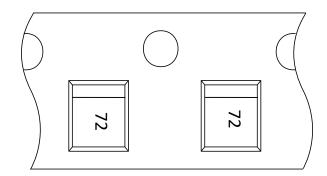
TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions







User Direction of Feed



IMPORTANT NOTICE

The information given in this document is believed to be accurate and reliable but shall in no event be regarded as a guarantee of conditions or characteristics.PN-Silicon assumes no responsibility for any errors in this document, or for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of PN-Silicon.

The product listed in this document are designed to be used with ordinary electronic equipment or devices and are not authorized to used with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, automotive and other safety device.)

The PN SILICON logo is a registered trademark of PN-Silicon co., ltd which reserves the right to make changes to the product or this document at any time without notice. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. PN-Silicon makes no warranty, representation or guarantee, express or implied, regarding the suitability of its products for any particular purpose. All rights reserved.